

Elder Alpes de Vasconcelos

List of Publications by Year in descending order

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57
papers

741
citations

567281

15
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580821

25
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57
all docs

57
docs citations

57
times ranked

920
citing authors

#	ARTICLE	IF	CITATIONS
1	A wrinkled ZnO/MCM-41 nanocomposite: hydrothermal synthesis and characterization. <i>Materials Research Express</i> , 2021, 8, 065011.	1.6	2
2	Synthesis and characterization of MCM-41 powder and its deposition by spin-coating. <i>Optik</i> , 2019, 185, 429-440.	2.9	15
3	Synthesis and characterization of carbon nanotubes/silica composites using gum arabic. <i>Materials Research Express</i> , 2018, 5, 075028.	1.6	2
4	A versatile technique to transfer multi-walled carbon nanotubes membranes to surfaces. <i>Translational Materials Research</i> , 2016, 3, 035001.	1.2	4
5	Metal-insulator-semiconductor capacitors with water-containing hexagonal mesoporous silica (MCM-41) dielectric and high values of capacitance per unit area. <i>Semiconductor Science and Technology</i> , 2015, 30, 045003.	2.0	6
6	Fabrication and electrical characterization of polyaniline/silicon carbide heterojunctions. <i>Journal Physics D: Applied Physics</i> , 2011, 44, 205101.	2.8	10
7	Electrical and microscopic characterization of ZnO films on p-SiC substrates. <i>Solid State Communications</i> , 2011, 151, 1252-1255.	1.9	12
8	Tailoring the Electrical Properties of ZnO/Polyaniline Heterostructures for Device Applications. <i>Journal of the Korean Physical Society</i> , 2011, 58, 1256-1260.	0.7	14
9	Potential of a simplified measurement scheme and device structure for a low cost label-free point-of-care capacitive biosensor. <i>Biosensors and Bioelectronics</i> , 2009, 25, 870-876.	10.1	62
10	A conducting polymer-silicon heterojunction as a new ultraviolet photodetector. <i>Applied Surface Science</i> , 2008, 255, 688-690.	6.1	15
11	Enhanced lifetime in porous silicon light-emitting diodes with fluorine doped tin oxide electrodes. <i>Thin Solid Films</i> , 2008, 517, 870-873.	1.8	35
12	A simplified reactive thermal evaporation method for indium tin oxide electrodes. <i>Applied Surface Science</i> , 2008, 255, 755-757.	6.1	30
13	Growth of sub-micron fibres of pure polyaniline using the electrospinning technique. <i>Journal Physics D: Applied Physics</i> , 2007, 40, 1068-1071.	2.8	49
14	Production of Ball-Lightning-Like Luminous Balls by Electrical Discharges in Silicon. <i>Physical Review Letters</i> , 2007, 98, 048501.	7.8	42
15	Immobilization of urease on vapour phase stain etched porous silicon. <i>Process Biochemistry</i> , 2007, 42, 429-433.	3.7	25
16	Nanowire growth on Si wafers by oxygen implantation and annealing. <i>Applied Surface Science</i> , 2006, 252, 5572-5574.	6.1	22
17	An improved description of the dielectric breakdown in oxides based on a generalized Weibull distribution. <i>Physica A: Statistical Mechanics and Its Applications</i> , 2006, 361, 209-215.	2.6	29
18	Thermal Lens Technique for the Determination of SiC Thermo-Optical Properties. <i>Materials Science Forum</i> , 2006, 527-529, 703-706.	0.3	1

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19	Statistical analysis of topographic images of nanoporous silicon and model surfaces. <i>Microelectronics Journal</i> , 2005, 36, 1011-1015.	2.0	7
20	Thermal-lens and photo-acoustic methods for the determination of SiC thermal properties. <i>Microelectronics Journal</i> , 2005, 36, 977-980.	2.0	15
21	Optical and electronic characterization of the band structure of blue methylene and rhodamine 6G-doped TiO ₂ sol-gel nanofilms. <i>Microelectronics Journal</i> , 2005, 36, 570-573.	2.0	9
22	Visible photoluminescence from Ge nanoclusters implanted in nanoporous aluminum oxide films. <i>Microelectronics Journal</i> , 2005, 36, 992-994.	2.0	5
23	Optical and electrical characterization of the band structure of polyaniline nanofilms and polyaniline/silicon heterojunctions. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2982-2985.	0.8	3
24	A new method for luminescent porous silicon formation: reaction-induced vapor-phase stain etch. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 1539-1542.	1.8	21
25	The Role of Non-abrupt Interfaces in SiC MOS Devices: Quantum Mechanical Simulations and Experiments. <i>AIP Conference Proceedings</i> , 2005, , .	0.4	0
26	Vapor-Phase Growth and Characterization of Luminescent Silicon Layers. <i>AIP Conference Proceedings</i> , 2005, , .	0.4	0
27	Spectroscopic characteristics of doped nanoporous aluminum oxide. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 112, 171-174.	3.5	20
28	Photoluminescence characteristics of rare earth-doped nanoporous aluminum oxide. <i>Applied Surface Science</i> , 2004, 234, 457-461.	6.1	16
29	Morphology of nanostructured luminescent silicon layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, S287-S290.	0.8	8
30	High-temperature thin-catalytic gate devices for combustion emissions control. <i>Brazilian Journal of Physics</i> , 2004, 34, 577-580.	1.4	3
31	Polyaniline nanofilms as a monitoring label and dosimetric device for gamma radiation. <i>Materials Characterization</i> , 2003, 50, 127-130.	4.4	20
32	AFM studies of polyaniline nanofilms irradiated with gamma rays. <i>Microelectronics Journal</i> , 2003, 34, 511-513.	2.0	10
33	Reliability physics study for semiconductor-polymer device development. <i>Microelectronics Journal</i> , 2003, 34, 713-715.	2.0	5
34	Polyaniline nanofilms as a sensing device for ionizing radiation. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 17, 666-667.	2.7	6
35	Gas response and modeling of NO-sensitive thin-Pt SiC schottky diodes. <i>Sensors and Actuators B: Chemical</i> , 2003, 92, 181-185.	7.8	15
36	NO Gas Detection at High Temperature Using Thin-Pt 4H-SiC and 6H-SiC Schottky Diodes. <i>Materials Science Forum</i> , 2003, 433-436, 961-964.	0.3	4

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37	Conducting Polymer/Silicon Heterojunction Diode for Gamma Radiation Detection. Radiation Protection Dosimetry, 2002, 101, 85-88.	0.8	16
38	Ionizing radiation and hot carrier effects in SiC MOS devices. Brazilian Journal of Physics, 2002, 32, 389-391.	1.4	2
39	Monte Carlo study of interfacial silicon suboxide layers and oxidation kinetics. Applied Surface Science, 2002, 190, 30-34.	6.1	1
40	The role of multiple damaged layers at the Si/SiO ₂ interface on the dielectric breakdown of MOS capacitors. Applied Surface Science, 2002, 190, 35-38.	6.1	2
41	A percolation based dielectric breakdown model with random changes in the dielectric constant. Physica A: Statistical Mechanics and Its Applications, 2002, 305, 351-359.	2.6	5
42	Fabrication of high quality silicon/polyaniline heterojunctions. Applied Surface Science, 2002, 190, 390-394.	6.1	45
43	A silicon-polymer heterostructure for sensor applications. Brazilian Journal of Physics, 2002, 32, 421-423.	1.4	11
44	X-Ray Radiation Response of Epitaxial and Nonepitaxial n-SiC Metal-Oxide-Semiconductor Capacitors. Japanese Journal of Applied Physics, 2001, 40, 2987-2990.	1.5	3
45	SiC/SiO ₂ interface states observed by x-ray photoelectron spectroscopy measurements under bias. Applied Physics Letters, 2001, 78, 96-98.	3.3	7
46	Dynamics of SiO ₂ /SiO _x /Si multilayer growth and interfacial effects on silicon quantum well confinement properties. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 74, 188-192.	3.5	4
47	Highly sensitive thermistors based on high-purity polycrystalline cubic silicon carbide. Sensors and Actuators A: Physical, 2000, 83, 167-171.	4.1	26
48	A study of silicon Schottky diode structures for NO _x gas detection. Sensors and Actuators B: Chemical, 2000, 65, 154-156.	7.8	33
49	Time evolution of SiO ₂ /Si interface defects and dopant passivation in MOS capacitors. Microelectronic Engineering, 2000, 51-52, 567-574.	2.4	8
50	Effect of ageing on x-ray induced dopant passivation in MOS capacitors. Semiconductor Science and Technology, 2000, 15, 794-798.	2.0	9
51	Dynamic Photocurrent Images of a Gas Sensing Surface. Japanese Journal of Applied Physics, 1999, 38, 2893-2898.	1.5	4
52	Post-irradiation dopant passivation in MOS capacitors exposed to high doses of x-rays. Semiconductor Science and Technology, 1998, 13, 1313-1316.	2.0	3
53	Potential of High-purity Polycrystalline Silicon Carbide for Thermistor Applications. Japanese Journal of Applied Physics, 1998, 37, 5078-5079.	1.5	8
54	NO ₂ Detection with Schottky Diodes and Heterojunction Structures. IEEE Transactions on Sensors and Micromachines, 1998, 118, 614-620.	0.1	0

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55	Highly Stable Tea Taste Detection Using SPV Method and Ion Electrodes. IEEJ Transactions on Sensors and Micromachines, 1998, 118, 608-613.	0.1	1
56	Correlation between dopant reduction and interfacial defects in low-energy x-ray-irradiated MOS capacitors. Semiconductor Science and Technology, 1997, 12, 1032-1037.	2.0	11
57	Silicon-carbide Schottky diodes with sputtered and laser-ablated thin-Pt gate as NO gas sensors in high temperature. , 0, , .		0